

Discrete POWER & Signal **Technologies**

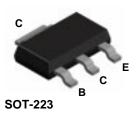
2N7052

2N7053

NZT7053







NPN Darlington Transistor

This device is designed for applications requiring extremely high gain at collector currents to 1.0 A and high breakdown voltage. Sourced from Process 06.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V_{CEO}	Collector-Emitter Voltage	100	V	
V _{CBO}	Collector-Base Voltage	100	V	
V _{EBO}	Emitter-Base Voltage	12	V	
I _C	Collector Current - Continuous	1.5	A	
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C	

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max		Units	
		2N7052	2N7053	*NZT7053	
P _D	Total Device Dissipation	625	1,000	1,000	mW
	Derate above 25°C	5.0	8.0	8.0	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	125		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	50	125	°C/W

^{*}Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm 2 .

These ratings are based on a maximum junction temperature of 150 degrees C.
 These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

NPN Darlington Transistor

(continued)

Electri	cal	Cha	racte	eristics
	vai	UII	1 400	<i>-</i> 1101101

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 1.0 \text{ mA}, I_B = 0$	100		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 100 \mu A, I_E = 0$	100		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 1.0 \text{ mA}, I_C = 0$	12		V
I _{CBO}	Collector-Cutoff Current	$V_{CB} = 80 \text{ V}, I_{E} = 0$		0.1	μΑ
I _{CES}	Collector-Cutoff Current	$V_{CE} = 80 \text{ V}, I_{E} = 0$		0.2	μΑ
I _{EBO}	Emitter-Cutoff Current	$V_{EB} = 7.0 \text{ V}, I_{C} = 0$		0.1	μΑ

ON CHARACTERISTICS*

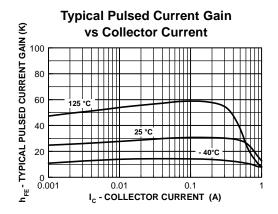
h _{FE}	DC Current Gain	$I_C = 100 \text{ mA}, V_{CE} = 5.0 \text{ V}$	10,000		
		$I_C = 1.0 \text{ A}, V_{CE} = 5.0 \text{ V}$	1,000	20,000	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_C = 100 \text{ mA}, I_B = 0.1 \text{ mA}$		1.5	V
V _{BE(on)}	Base-Emitter On Voltage	$I_C = 100 \text{ mA}, V_{BE} = 5.0 \text{ V}$		2.0	V

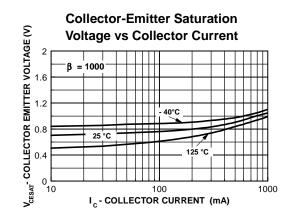
SMALL SIGNAL CHARACTERISTICS

F _T	Transition Frequency	$I_C = 100 \text{ mA}, V_{CE} = 5.0 \text{ V},$	200		MHz
C _{cb}	Collector-Base Capacitance	V _{CB} = 10 V,f = 1.0 MHz 2N7052		10	pF
		2N7053		8.0	

^{*}Pulse Test: Pulse Width £ 300 ms, Duty Cycle £ 1.0%

Typical Characteristics

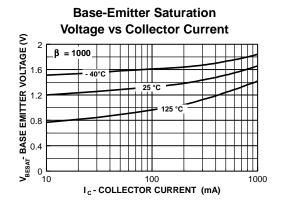


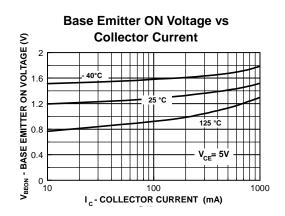


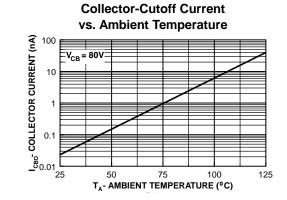
NPN Darlington Transistor

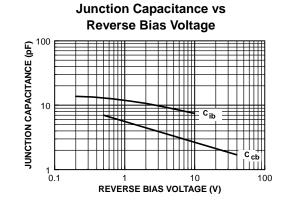
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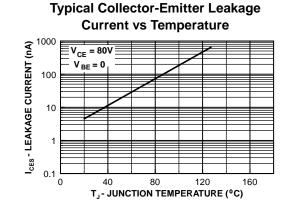
Typical Characteristics (continued)

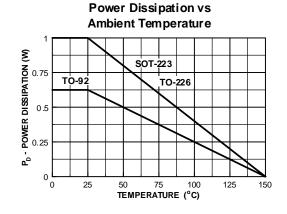










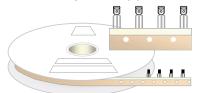


TO-92 Tape and Reel Data FAIRCHILD SEMICONDUCTOR TM **TO-92 Packaging** Configuration: Figure 1.0 **TAPE and REEL OPTION** FSCINT Label sample See Fig 2.0 for various Reeling Styles CBVK//418019 **FSCINT** Label 5 Reels per Intermediate Box Customized F63TNR Label sample Label F63TNR LOT: CBVK741B019 QTY: 2000 FSID: PN222N Customized QTY1: QTY2: Label 375mm x 267mm x 375mm Intermediate Box TO-92 TNR/AMMO PACKING INFROMATION **AMMO PACK OPTION** See Fig 3.0 for 2 Ammo Packing Style Quantity EOL code **Pack Options** 2,000 D26Z Е 2,000 D27Z Ammo М 2,000 D74Z D75Z 2,000 **FSCINT** Unit weight = 0.22 gm Reel weight with components = 1.04 kg Ammo weight with components = 1.02 kg Max quantity per intermediate box = 10,000 units Label 5 Ammo boxes per Intermediate Box 327mm x 158mm x 135mm Immediate Box Customized F63TNR Customized Label Label 333mm x 231mm x 183mm Intermediate Box (TO-92) BULK PACKING INFORMATION **BULK OPTION** See Bulk Packing DESCRIPTION QUANTITY Information table J18Z TO-18 OPTION STD 2.0 K / BOX Anti-static Bubble Sheets TO-5 OPTION STD NO LEAD CLIP 1.5 K / BOX J05Z **FSCINT Label** NO EOL TO-92 STANDARD STRAIGHT FOR: PKG 92, NO LEADCLIP 2.0 K / BOX 94 (NON PROELECTRON SERIES), 96 TO-92 STANDARD STRAIGHT FOR: PKG 94 (PROELECTRON SERIES BCXXX, BFXXX, BSRXXX), 97, 98 L34Z NO LEADCLIP 2.0 K / BOX 2000 units per 114mm x 102mm x 51mm EO70 box for std option Immediate Box 5 EO70 boxes per intermediate Box 530mm x 130mm x 83mm Customized Intermediate box Label FSCINT Label 10,000 units maximum per intermediate box for std option

TO-92 Tape and Reel Data, continued

TO-92 Reeling Style Configuration: Figure 2.0

Machine Option "A" (H)

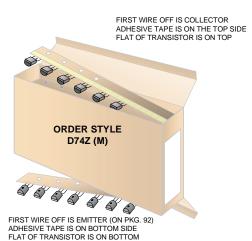


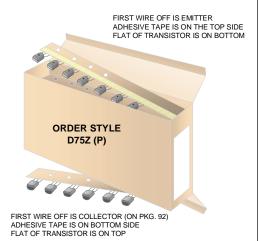
Style "A", D26Z, D70Z (s/h)

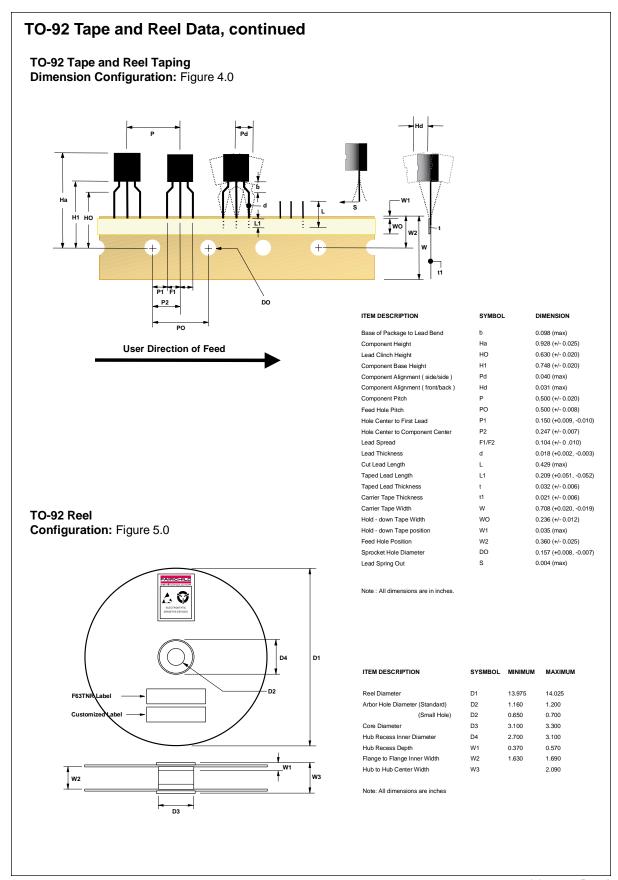
Machine Option "E" (J)

Style "E", D27Z, D71Z (s/h)

TO-92 Radial Ammo Packaging Configuration: Figure 3.0



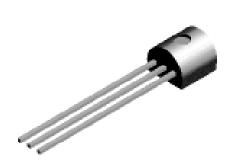


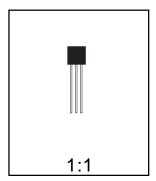


TO-92 Package Dimensions



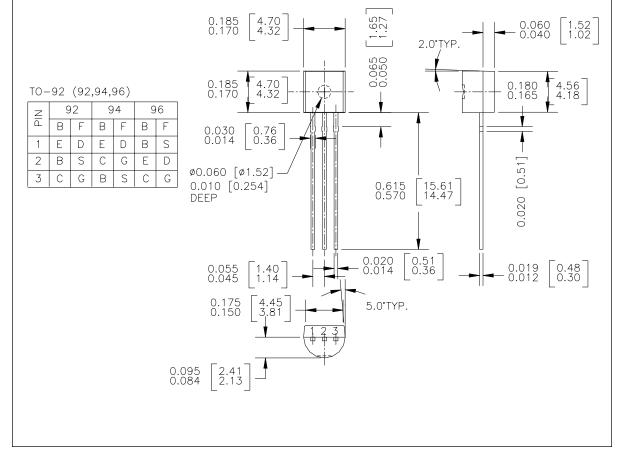
TO-92 (FS PKG Code 92, 94, 96)





Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.1977



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DOME™ ISOPLANAR™ Quiet Series™

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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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